

IRFB812PbF

HEXFET® Power MOSFET

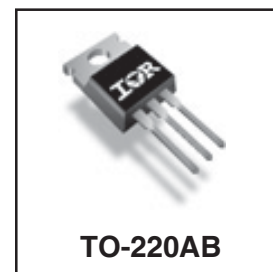
Applications

- Zero Voltage Switching SMPS
- Uninterruptible Power Supplies
- Motor Control applications

V_{DSS}	$R_{DS(on)}$ typ.	T_{rr} typ.	I_D
500V	1.75Ω	75ns	3.6A

Features and Benefits

- Fast body diode eliminates the need for external diodes in ZVS applications.
- Lower Gate charge results in simpler drive requirements.
- Higher Gate voltage threshold offers improved noise immunity.



Absolute Maximum Ratings

	Parameter	Max.	Units
I_D @ $T_C = 25^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	3.6	A
I_D @ $T_C = 100^\circ\text{C}$	Continuous Drain Current, V_{GS} @ 10V	2.3	
I_{DM}	Pulsed Drain Current ①	14.4	
P_D @ $T_C = 25^\circ\text{C}$	Power Dissipation	78	W
	Linear Derating Factor	0.63	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery dv/dt ③	32	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to + 150	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw	10lb·in (1.1N·m)	

Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	3.6	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	14.4		
V_{SD}	Diode Forward Voltage	—	—	1.2	V	$T_J = 25^\circ\text{C}$, $I_S = 3.6\text{A}$, $V_{GS} = 0\text{V}$ ④
t_{rr}	Reverse Recovery Time	—	75	110	ns	$T_J = 25^\circ\text{C}$, $I_F = 3.6\text{A}$
		—	94	140		$T_J = 125^\circ\text{C}$, $di/dt = 100\text{A}/\mu\text{s}$ ④
Q_{rr}	Reverse Recovery Charge	—	135	200	nC	$T_J = 25^\circ\text{C}$, $I_S = 3.6\text{A}$, $V_{GS} = 0\text{V}$ ④
		—	220	330		$T_J = 125^\circ\text{C}$, $di/dt = 100\text{A}/\mu\text{s}$ ④
I_{RRM}	Reverse Recovery Current	—	3.2	4.8	A	$T_J = 25^\circ\text{C}$
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes ① through ⑥ are on page 2

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Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	500	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.37	—	V/°C	Reference to 25°C , $I_D = 250\mu A$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	1.75	2.2	Ω	$V_{GS} = 10V, I_D = 2.2A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	3.0	—	5.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 500V, V_{GS} = 0V$
		—	—	2.0	mA	$V_{DS} = 400V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100	nA	$V_{GS} = -20V$

Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	7.6	—	—	S	$V_{DS} = 50V, I_D = 2.2A$
Q_g	Total Gate Charge	—	—	20	nC	$I_D = 3.6A$
Q_{gs}	Gate-to-Source Charge	—	—	7.3	nC	$V_{DS} = 400V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	7.1	nC	$V_{GS} = 10V$, See Fig.14a & 14b ④
$t_{d(on)}$	Turn-On Delay Time	—	14	—	ns	$V_{DD} = 250V$
t_r	Rise Time	—	22	—	ns	$I_D = 3.6A$
$t_{d(off)}$	Turn-Off Delay Time	—	24	—	ns	$R_G = 17\Omega$
t_f	Fall Time	—	17	—	ns	$V_{GS} = 10V$, See Fig. 15a & 15b ④
C_{iss}	Input Capacitance	—	810	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	47	—	pF	$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	7.3	—	pF	$f = 1.0MHz$, See Fig. 5
C_{oss}	Output Capacitance	—	610	—	pF	$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0MHz$
C_{oss}	Output Capacitance	—	16	—	pF	$V_{GS} = 0V, V_{DS} = 400V, f = 1.0MHz$
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	5.9	—	pF	$V_{GS} = 0V, V_{DS} = 0V \text{ to } 400V$ ⑤
$C_{oss \text{ eff. (ER)}}$	Effective Output Capacitance (Energy Related)	—	37	—	pF	

Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	150	mJ
I_{AR}	Avalanche Current ①	—	1.8	A
E_{AR}	Repetitive Avalanche Energy ①	—	7.8	mJ

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case ⑥	—	1.6	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.5	—	°C/W
$R_{\theta JA}$	Junction-to-Ambient ⑥	—	62	°C/W

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See Fig. 11)
- ② Starting $T_J = 25^\circ\text{C}$, $L = 93mH$, $R_G = 25\Omega$, $I_{AS} = 1.8A$. (See Figure 13).
- ③ $I_{SD} = 3.6A$, $di/dt \leq 520A/\mu s$, $V_{DD} V_{(BR)DSS}$, $T_J \leq 150^\circ\text{C}$.

④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.

⑤ $C_{oss \text{ eff.}}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

$C_{oss \text{ eff. (ER)}}$ is a fixed capacitance that stores the same energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⑥ R_{θ} is measured at T_J approximately 90°C

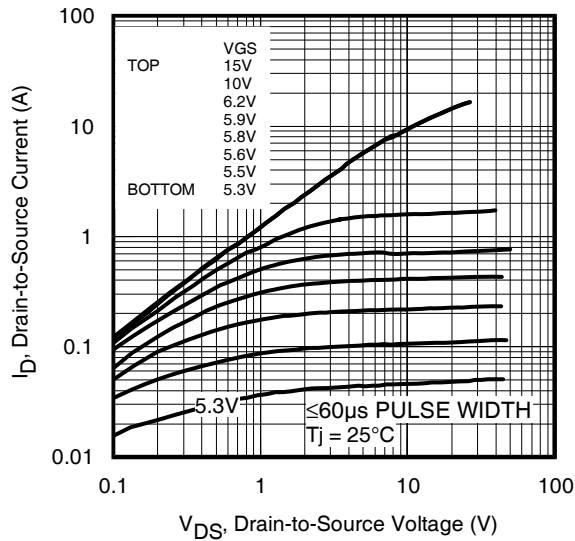


Fig 1. Typical Output Characteristics

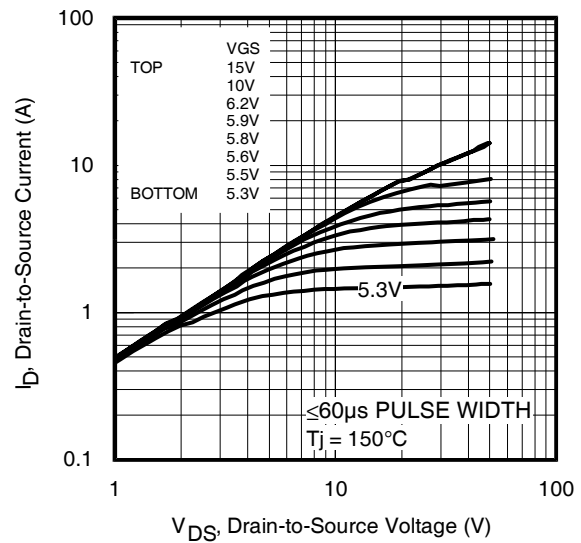


Fig 2. Typical Output Characteristics

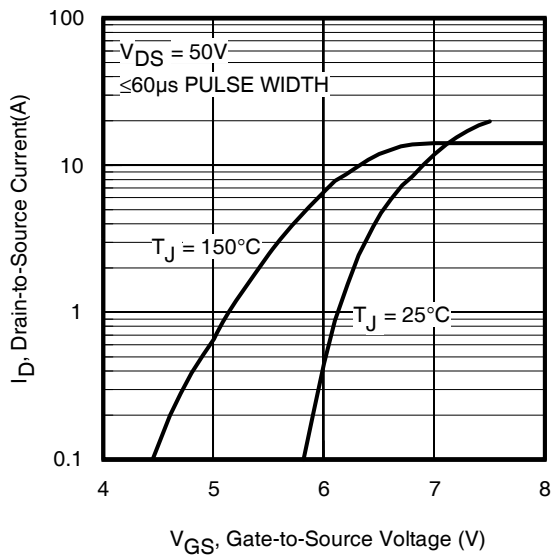


Fig 3. Typical Transfer Characteristics

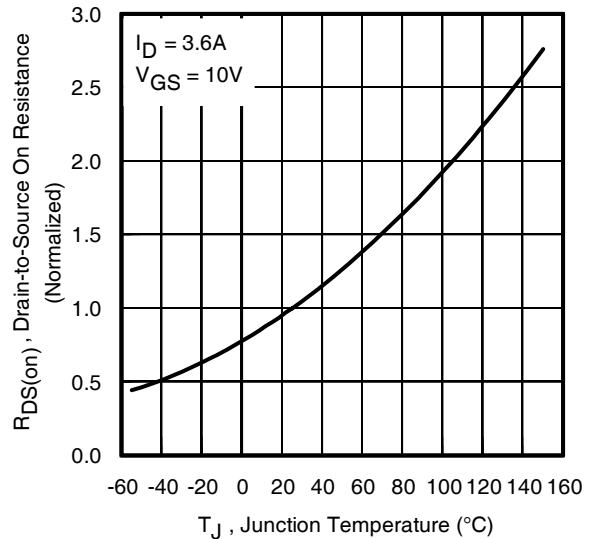


Fig 4. Normalized On-Resistance Vs. Temperature

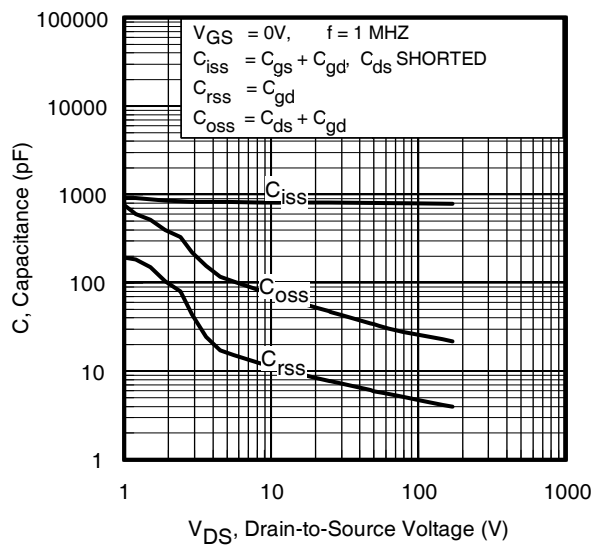


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

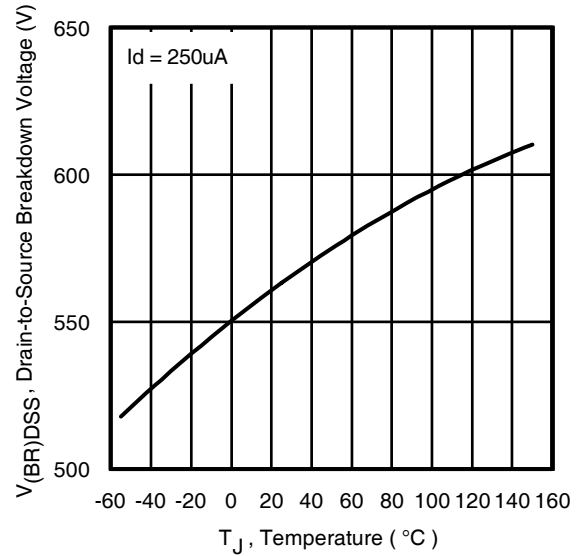
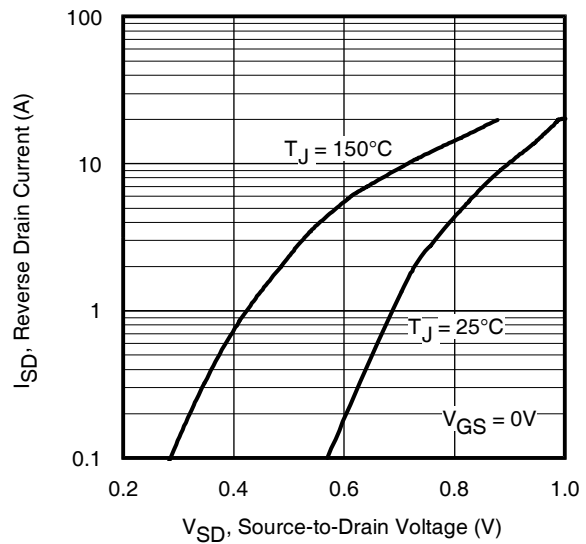
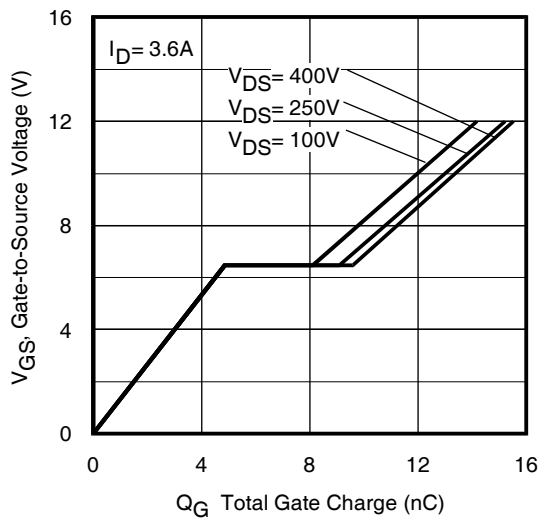


Fig 6. Typ. Breakdown Voltage vs. Temperature



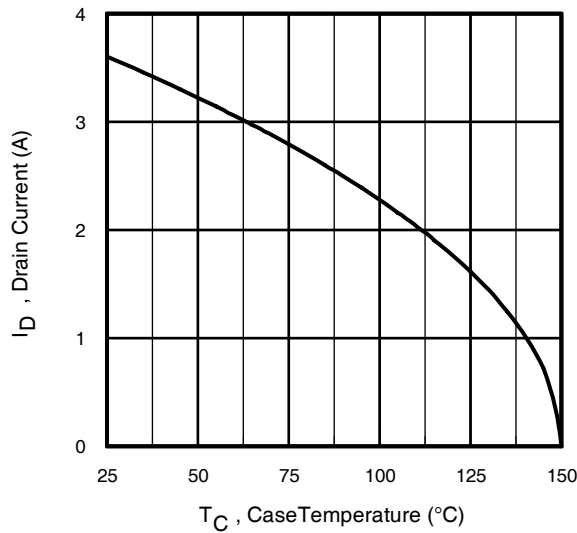


Fig 9. Maximum Drain Current Vs. Case Temperature

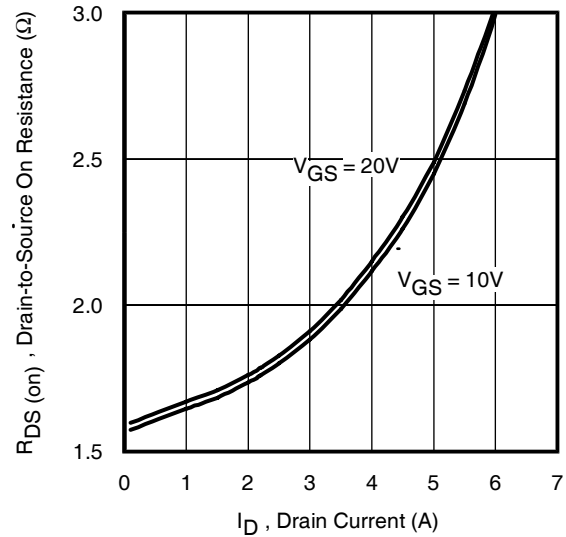


Fig 9. Typical $R_{DS(on)}$ Vs. Drain Current

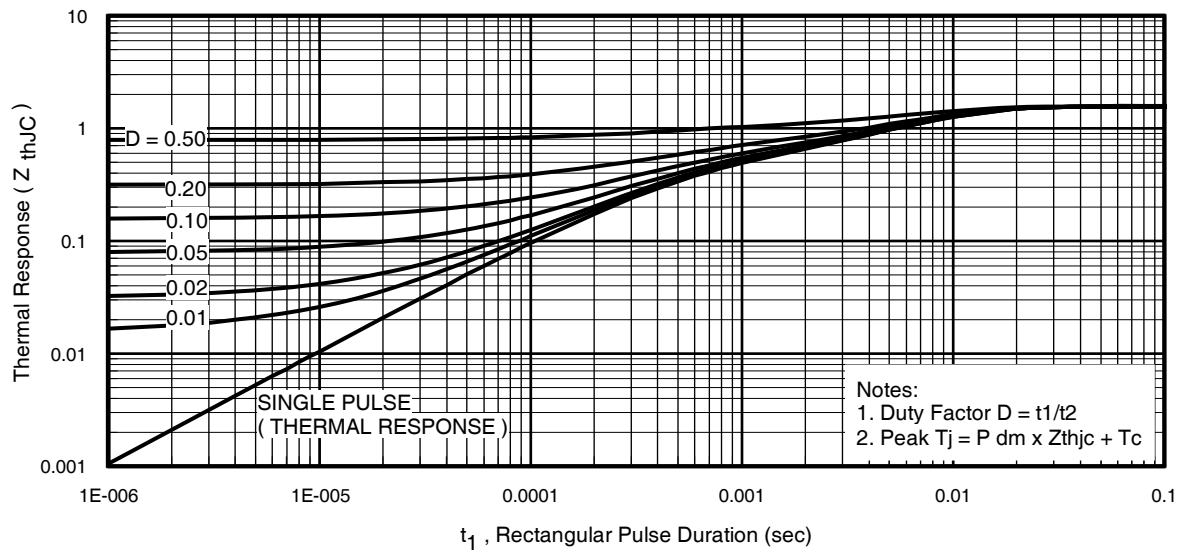


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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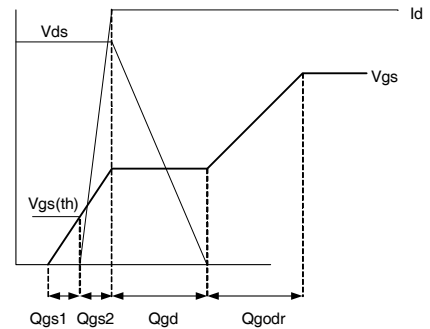
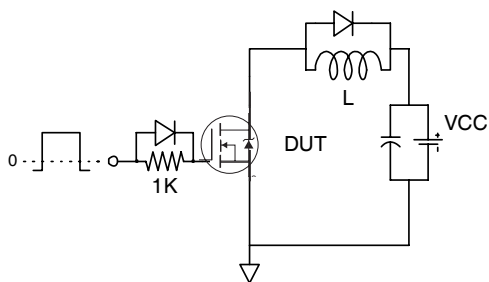
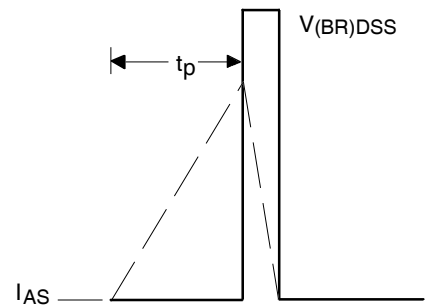
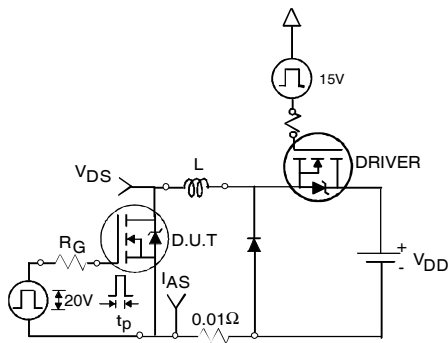
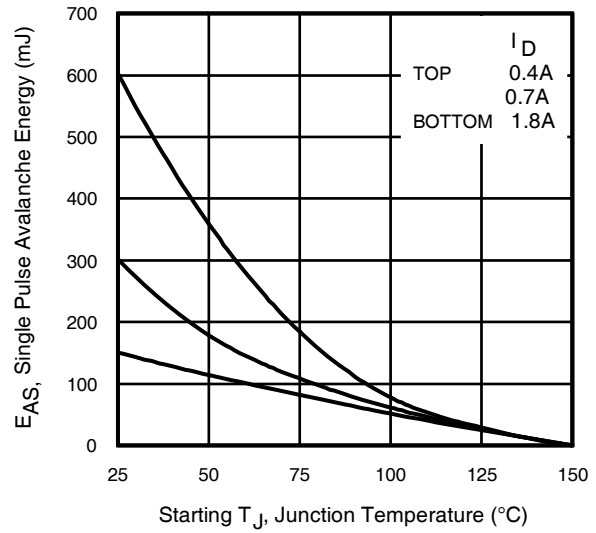
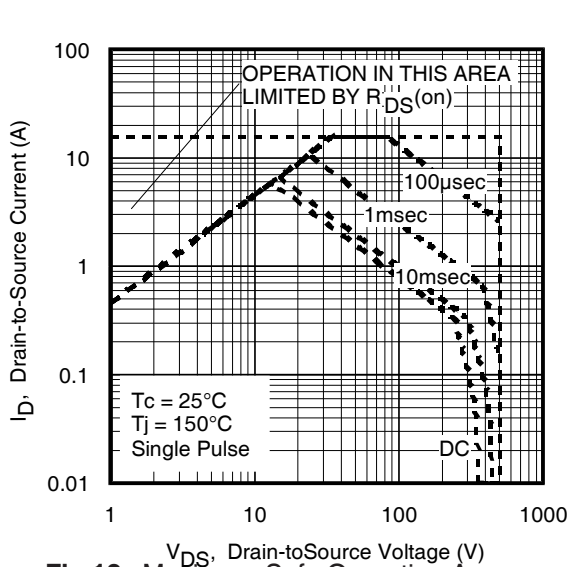


Fig 14a. Gate Charge Test Circuit

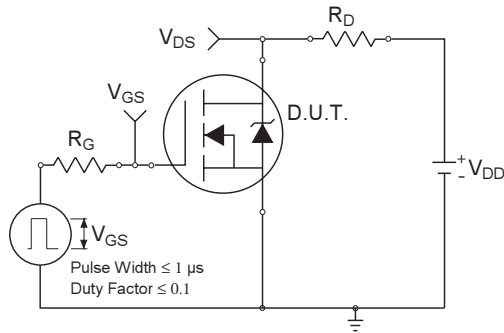


Fig 15a. Switching Time Test Circuit

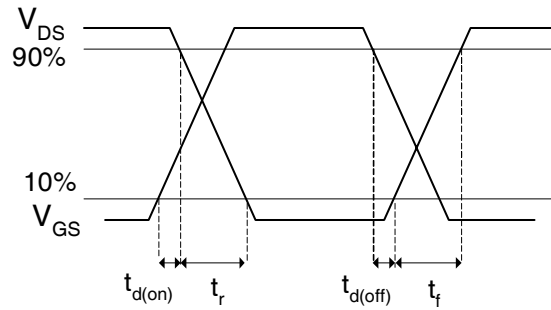


Fig 15b. Switching Time Waveforms

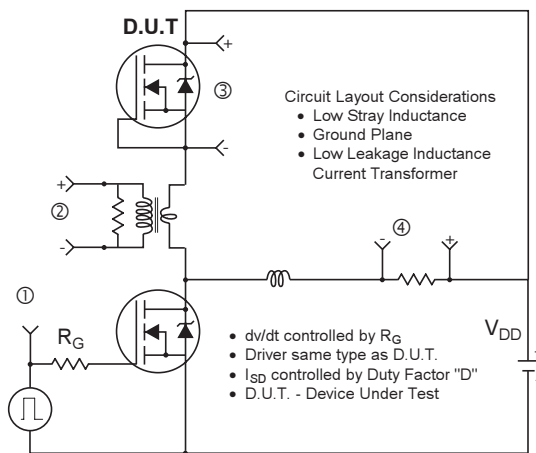
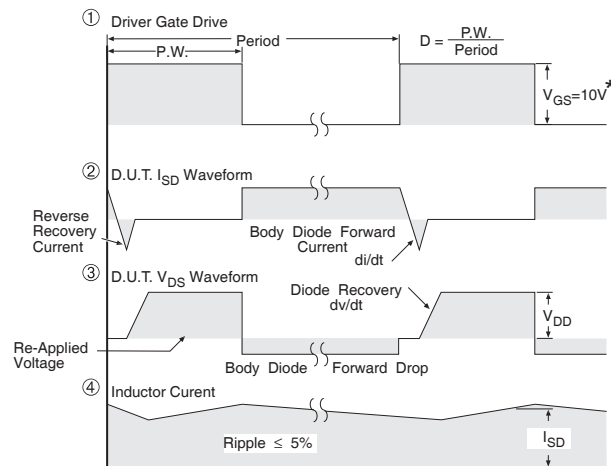


Fig 16. Peak Diode Recovery dv/dt Test Circuit for N-Channel
HEXFET® Power MOSFETs



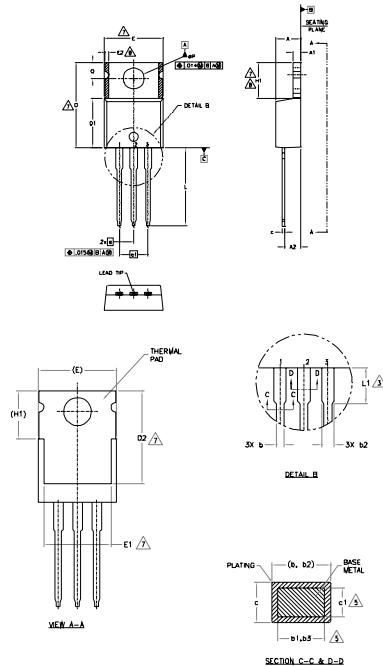
* $V_{GS} = 5V$ for Logic Level Devices

IRFB812PbF

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)

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- NOTES:
- 1.- DIMENSIONING AND TOLERANCING AS PER ASME Y14.5 M- 1994
 - 2.- DIMENSIONS ARE SHOWN IN INCHES (MILLIMETERS)
 - 3.- LEAD DIMENSION AND FINISH UNCONTROLLED IN LT
 - 4.- DIMENSION D, DT & E DO NOT INCLUDE WELD FLASH; WELD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
 - 5.- DIMENSION B1, B2 & C1 APPLY TO BASE METAL ONLY.
 - 6.- CONTROLLING DIMENSION IS INCHES.
 - 7.- THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS E, H1, D2 & E1
 - 8.- DIMENSION E2 X H1 DEFINE A ZONE WHERE STAMPING AND SINGULATION IRREGULARITIES ARE ALLOWED.
 - 9.- OUTLINE CONFORMS TO JEDEC TO-220, EXCEPT A2 (max.) AND D2 (min.) WHERE DIMENSIONS ARE DERIVED FROM THE ACTUAL PACKAGE OUTLINE.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	3.56	4.83	.140	.190	
A1	0.51	1.40	.020	.055	
A2	2.03	2.92	.080	.115	
b	0.38	1.01	.015	.040	
b1	0.38	0.97	.015	.038	5
b2	1.14	1.78	.045	.070	
b3	1.14	1.73	.045	.068	5
c	0.36	0.61	.014	.024	
c1	0.36	0.56	.014	.022	5
D	14.22	16.51	.560	.650	4
D1	8.38	9.02	.330	.355	
D2	11.58	12.88	.460	.507	7
E	9.65	10.67	.380	.420	4,7
E1	6.86	8.89	.270	.350	7
E2	-	0.76	-	.030	8
e	2.54 BSC		.100 BSC		
e1	2.54 BSC		.100 BSC		
H1	5.84	6.86	.230	.270	7,8
L	12.70	14.73	.500	.580	
L1	3.56	4.06	.140	.160	5
MP	3.54	4.08	.139	.161	
Q	2.54	3.42	.100	.135	

LEAD ASSIGNMENTS

- JEDEC
- 1.- GATE
 - 2.- DRAIN
 - 3.- SOURCE

OPTIONAL SYMBOLS

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER

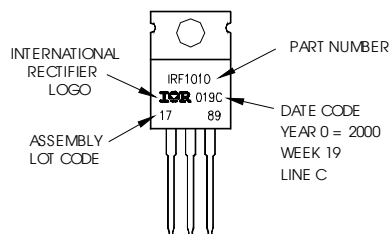
DOES

- 1.- INDEX
- 2.- DIMENSE
- 3.- INDEX

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 2000
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position
indicates "Lead - Free"



TO-220AB packages are not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Data and specifications subject to change without notice.
This product has been designed and qualified for the Industrial market.
Qualification Standards can be found on IR's Web site.

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IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
TAC Fax: (310) 252-7903

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